

50A, 700V - 1000V Hyperfast Diodes

RHRU5070, RHRU5080, RHRU5090 and RHRU50100 (TA49066) are hyperfast diodes with soft recovery characteristics ($t_{RR} < 75\text{ns}$). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Ordering Information

PACKAGING AVAILABILITY

| PART NUMBER | PACKAGE | BRAND |
|-------------|---------|-----------|
| RHRU5070 | TO-218 | RHRU5070 |
| RHRU5080 | TO-218 | RHRU5080 |
| RHRU5090 | TO-218 | RHRU5090 |
| RHRU50100 | TO-218 | RHRU50100 |

NOTE: When ordering, use the entire part number.

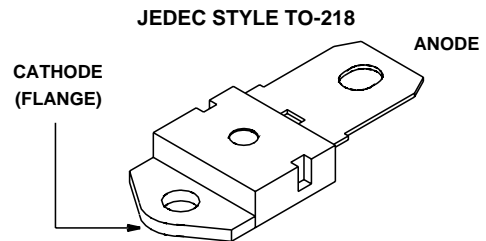
Features

- Hyperfast with Soft Recovery<75ns
- Operating Temperature +175°C
- Reverse Voltage Up To.....1000V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Package



Symbol



Absolute Maximum Ratings $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

| | RHRU5070 | RHRU5080 | RHRU5090 | RHRU50100 | UNITS |
|--|----------------------------|-------------|-------------|-------------|------------------|
| Peak Repetitive Reverse Voltage | V_{RRM} 700 | 800 | 900 | 1000 | V |
| Working Peak Reverse Voltage..... | V_{RWM} 700 | 800 | 900 | 1000 | V |
| DC Blocking Voltage | V_R 700 | 800 | 900 | 1000 | V |
| Average Rectified Forward Current | $I_{F(AV)}$ 50 | 50 | 50 | 50 | A |
| ($T_C = +65^\circ\text{C}$) | | | | | |
| Repetitive Peak Surge Current | I_{FSM} 100 | 100 | 100 | 100 | A |
| (Square Wave, 20kHz) | | | | | |
| Nonrepetitive Peak Surge Current | I_{FSM} 500 | 500 | 500 | 500 | A |
| (Halfwave, 1 Phase, 60Hz) | | | | | |
| Maximum Power Dissipation..... | P_D 150 | 150 | 150 | 150 | W |
| Avalanche Energy ($L = 40\text{mH}$) | E_{AVL} 40 | 40 | 40 | 40 | mj |
| Operating and Storage Temperature..... | T_{STG}, T_J -65 to +175 | -65 to +175 | -65 to +175 | -65 to +175 | $^\circ\text{C}$ |

RHRU5070, RHRU5080, RHRU5090, RHRU50100

Electrical Specifications $T_C = +25^\circ\text{C}$, Unless Otherwise Specified

| SYMBOL | TEST CONDITION | RHRU5070 | | | RHRU5080 | | | RHRU5090 | | | RHRU50100 | | | UNITS |
|-----------------|---|----------|-----|-----|----------|-----|-----|----------|-----|-----|-----------|-----|-----|---------------------------|
| | | MIN | TYP | MAX | MIN | TYP | MAX | MIN | TYP | MAX | MIN | TYP | MAX | |
| V_F | $I_F = 50\text{A}, T_C = +25^\circ\text{C}$ | - | - | 3.0 | - | - | 3.0 | - | - | 3.0 | - | - | 3.0 | V |
| | $I_F = 50\text{A}, T_C = +150^\circ\text{C}$ | - | - | 2.5 | - | - | 2.5 | - | - | 2.5 | - | - | 2.5 | V |
| I_R | $V_R = 700\text{V}, T_C = +25^\circ\text{C}$ | - | - | 500 | - | - | - | - | - | - | - | - | - | μA |
| | $V_R = 800\text{V}, T_C = +25^\circ\text{C}$ | - | - | - | - | - | 500 | - | - | - | - | - | - | μA |
| | $V_R = 900\text{V}, T_C = +25^\circ\text{C}$ | - | - | - | - | - | - | - | - | 500 | - | - | - | μA |
| | $V_R = 1000\text{V}, T_C = +25^\circ\text{C}$ | - | - | - | - | - | - | - | - | - | - | - | 500 | μA |
| I_R | $V_R = 700\text{V}, T_C = +150^\circ\text{C}$ | - | - | 3.0 | - | - | - | - | - | - | - | - | - | mA |
| | $V_R = 800\text{V}, T_C = +150^\circ\text{C}$ | - | - | - | - | - | 3.0 | - | - | - | - | - | - | mA |
| | $V_R = 900\text{V}, T_C = +150^\circ\text{C}$ | - | - | - | - | - | - | - | - | 3.0 | - | - | - | mA |
| | $V_R = 1000\text{V}, T_C = +150^\circ\text{C}$ | - | - | - | - | - | - | - | - | - | - | - | 3.0 | mA |
| t_{RR} | $I_F = 1\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$ | - | - | 75 | - | - | 75 | - | - | 75 | - | - | 75 | ns |
| | $I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$ | - | - | 95 | - | - | 95 | - | - | 95 | - | - | 95 | ns |
| t_A | $I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$ | - | 54 | - | - | 54 | - | - | 54 | - | - | 54 | - | ns |
| t_B | $I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$ | - | 32 | - | - | 32 | - | - | 32 | - | - | 32 | - | ns |
| Q_{RR} | $I_F = 50\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$ | - | 125 | - | - | 125 | - | - | 125 | - | - | 125 | - | nC |
| C_J | $V_R = 10\text{V}, I_F = 0\text{A}$ | - | 150 | - | - | 150 | - | - | 150 | - | - | 150 | - | pF |
| $R_{\theta JC}$ | | - | - | 1.0 | - | - | 1.0 | - | - | 1.0 | - | - | 1.0 | $^\circ\text{C}/\text{W}$ |

DEFINITIONS

V_F = Instantaneous forward voltage ($p_w = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current.

t_{RR} = Reverse recovery time (Figure 2), summation of $t_A + t_B$.

t_A = Time to reach peak reverse current (See Figure 2).

t_B = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 2).

$R_{\theta JC}$ = Thermal resistance junction to case.

E_{AVL} = Controlled avalanche energy (See Figure 10 and Figure 11).

p_w = Pulse width.

D = Duty cycle.

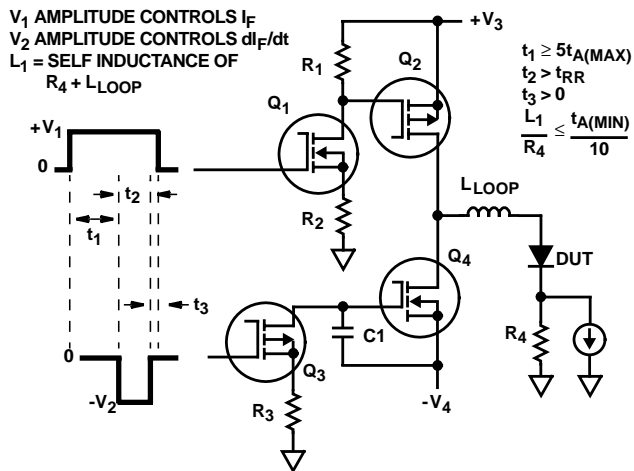


FIGURE 1. t_{RR} TEST CIRCUIT

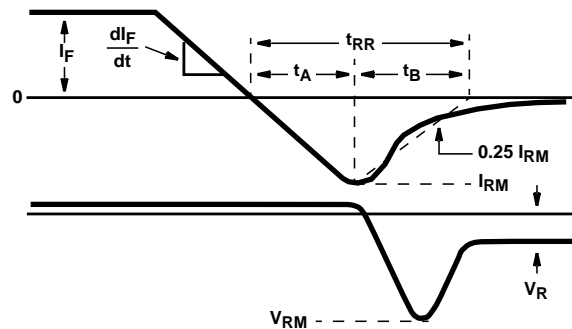


FIGURE 2. WAVEFORMS AND DEFINITIONS

Typical Performance Curves

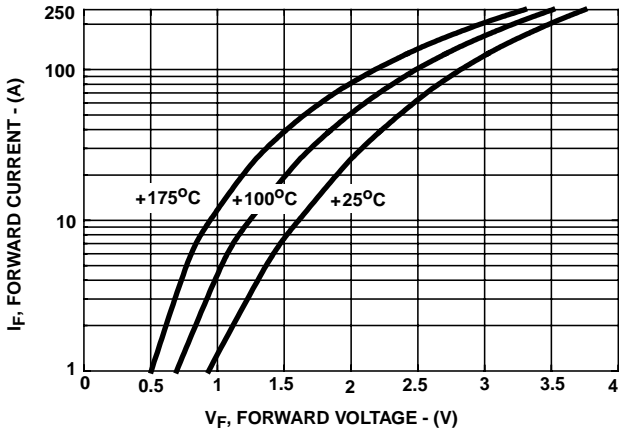


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

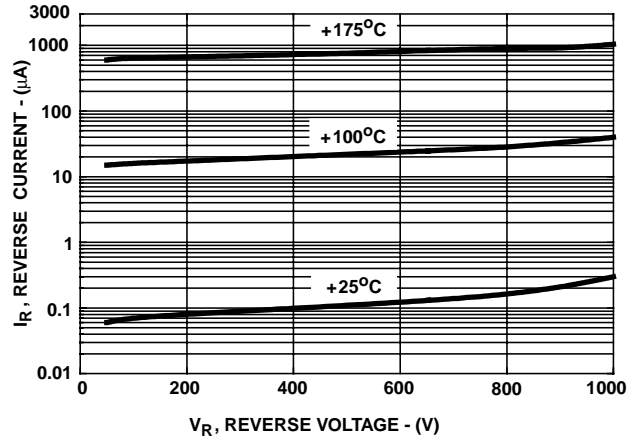


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

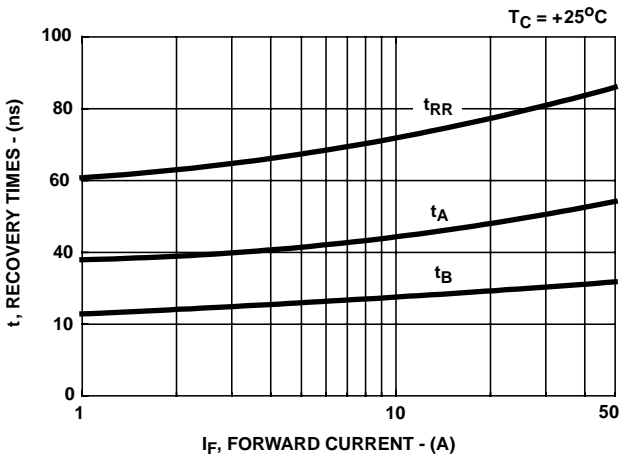


FIGURE 5. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +25°C

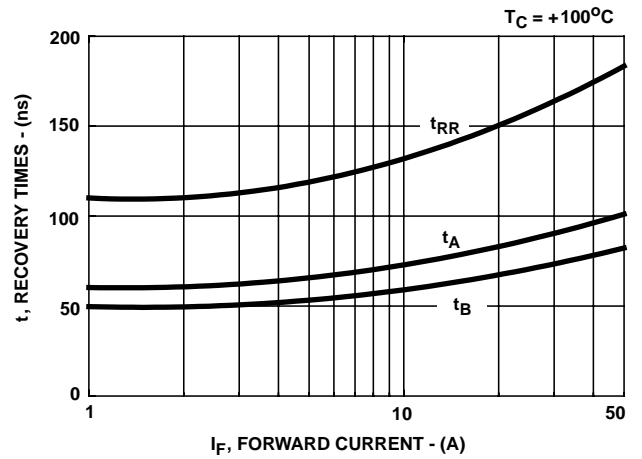


FIGURE 6. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +100°C

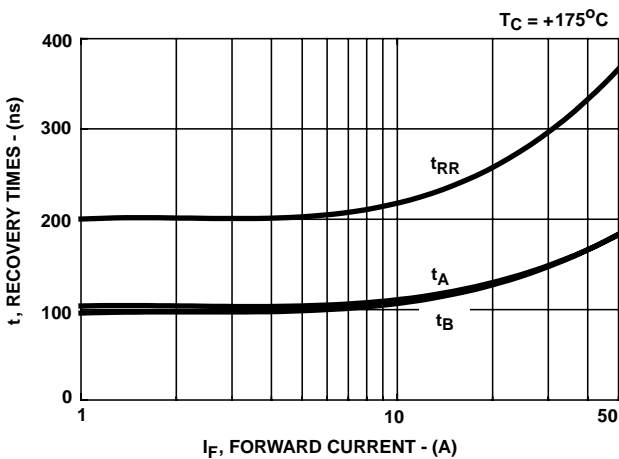


FIGURE 7. TYPICAL t_{RR} , t_A AND t_B CURVES vs FORWARD CURRENT AT +175°C

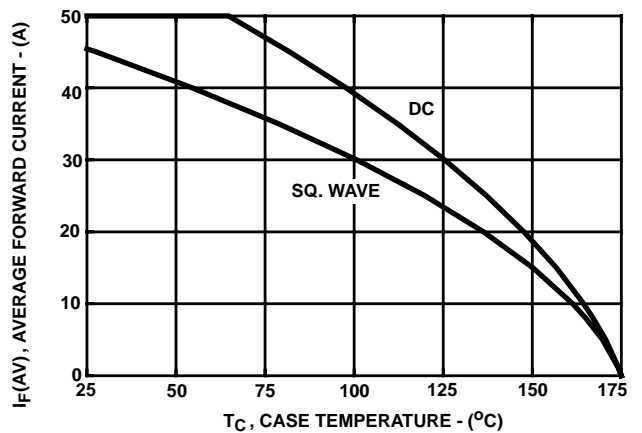


FIGURE 8. CURRENT DERATING CURVE FOR ALL TYPES

Typical Performance Curves (Continued)

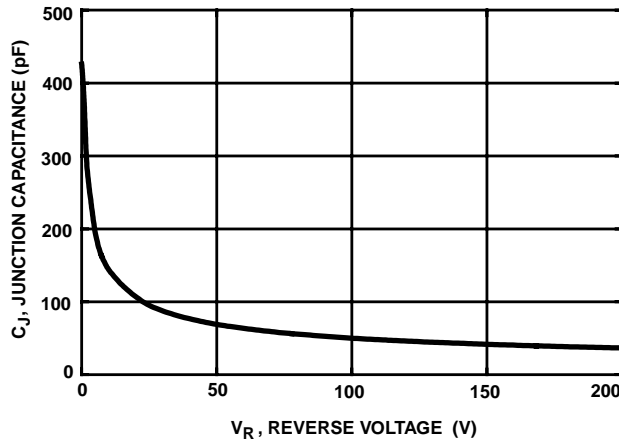


FIGURE 9. TYPICAL JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuit and Waveforms

$I_{MAX} = 1A$
 $L = 40mH$
 $R < 0.1\Omega$
 $E_{AVL} = 1/2LI^2[V_{AVL}/(V_{AVL} - V_{DD})]$
 Q1 AND Q2 ARE 1000V MOSFETS

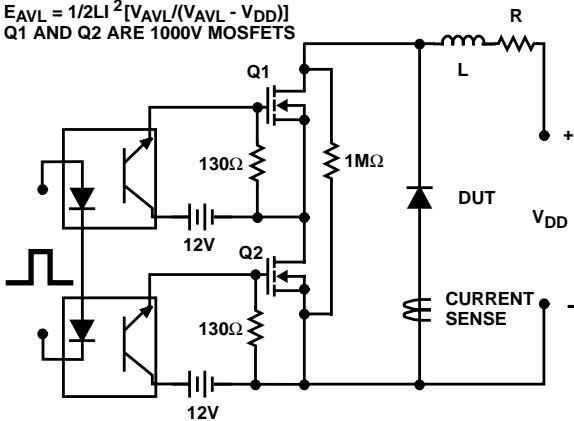


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

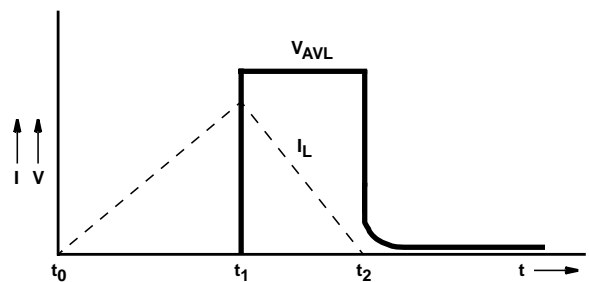


FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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